2N3583 2N3584 2N3585

SILICON NPN TRANSISTORS



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3583 series devices are silicon NPN transistors designed for high speed switching and high voltage amplifier applications.





MAXIMUM RATINGS: (T _C =25°C)	SYMBOL	<u>2N3583</u>	2N3584	2N3585	UNITS
Collector-Base Voltage	V_{CBO}	250	375	500	V
Collector-Emitter Voltage	VCEO	175	250	300	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	6.0	V
Continuous Collector Current	IC	1.0	2.0	2.0	Α
Peak Collector Current	ICM		5.0		Α
Continuous Base Current	Ι _Β		1.0		Α
Power Dissipation	P_{D}		35		W
Operating and Storage Junction Temperature	T _J , T _{stg}		-65 to +200		°C
Thermal Resistance	⊚JC		5.0		°C/W

$\textbf{ELECTRICAL CHARACTERISTICS:} \ (\textbf{T}_{\hbox{C}} = 25^{\circ} \text{C unless otherwise noted})$

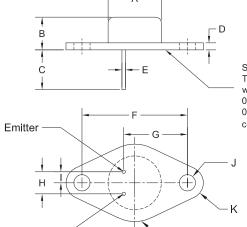
ELECTRICA	AL CHARACTERISTICS: (TC-25 C unless of		se note		3584	2112	3585	
SYMBOL	TEST CONDITIONS		MAX		MAX		MAX	UNITS
ICEV	V _{CE} =225V, V _{EB} =1.5V	-	1.0	-	-	-	-	mA
ICEV	V _{CE} =340V, V _{EB} =1.5V	-	-	_	1.0	_	-	mA
ICEV	V _{CE} =450V, V _{EB} =1.5V	-	-	-	-	-	1.0	mA
ICEV	V _{CE} =225V, V _{EB} =1.5V, T _C =150°C	-	3.0	-	-	-	-	mA
ICEV	V _{CE} =300V, V _{EB} =1.5V, T _C =150°C	-	-	-	3.0	-	3.0	mA
ICEO	V _{CE} =150V	-	10	-	5.0	-	5.0	mA
I _{EBO}	V _{BE} =6.0V	-	5.0	-	0.5	-	0.5	mA
BVCEO	I _C =200mA	175	-	250	-	300	-	V
V _{CE} (SAT)	I _C =1.0A, I _B =125mA	-	5.0	-	0.75	-	0.75	V
V _{BE} (SAT)	I _C =1.0A, I _B =100mA	-	-	-	1.4	-	1.4	V
V _{BE} (ON)	V _{CE} =10V, I _C =1.0A	-	1.4	-	1.4	-	1.4	V
hFE	V _{CE} =10V, I _C =100mA	40	-	40	-	40	-	
h _{FE}	V _{CE} =10V, I _C =500mA	40	200	-	-	-	-	
hFE	V _{CE} =2.0V, I _C =1.0A	-	-	8.0	80	8.0	80	
hFE	V _{CE} =10V, I _C =1.0A	10	-	25	100	25	100	
f_{T}	V _{CE} =10V, I _C =200mA, f=5.0MHz	10	-	10	-	10	-	MHz
C_{ob}	V _{CB} =10V, I _E =0, f=1.0MHz	-	120	-	120	-	120	pF
h _{fe}	V _{CE} =30V, I _C =100mA, f=1.0kHz	25	350	-	-	-	-	
t _r	V_{CC} =200V, I_{C} =1.0A, I_{B1} =100mA, R_{L} =200 Ω	-	-	-	3.0	-	3.0	μs
t _S	V _{CC} =200V, I _C =1.0A, I _{B1} =I _{B2} =100mA	-	-	-	4.0	-	4.0	μs
t _f	V _{CC} =200V, I _C =1.0A, I _{B1} =I _{B2} =100mA	-	-	-	3.0	-	3.0	μs
l _{S/b}	V _{CE} =100V	350	-	350	-	350	-	mA
						R3	(2-Sep	tember 20

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TO-66 CASE - MECHANICAL OUTLINE



Seating Plane: The seating plane must be within 0.001" concave to 0.004" convex within 0.600" diameter from the center of the device.

MARKING: FULL PART NUMBER

Base

DIMENSIONS								
	INC	HES	MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
A (DIA)	0.470	0.500	11.94	12.70				
В	0.250	0.340	6.35	8.64				
С	0.360	-	9.14	-				
D	0.050	0.075	1.27	1.91				
E (DIA)	0.028	0.034	0.71	0.86				
F	0.956	0.964	24.28	24.48				
G	0.570	0.590	14.48	14.99				
Н	0.190	0.210	4.83	5.33				
	0.093	0.107	2.36	2.72				
J (DIA)	0.142	0.152	3.61	3.86				
K (RAD)	0.141		3.58					
L (RAD)	0.345		8.76					

R3

TO-66 (REV:R3)

R3 (2-September 2014)



OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- · Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- · PbSn plating options
- · Package details
- · Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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